

Vibhor Kumar

List of Publications by Year in descending order

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759233

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#	ARTICLE	IF	CITATIONS
1	Interface improvement of epitaxial 4H-SiC based Schottky diodes by selective heavy ion irradiation. Applied Nanoscience (Switzerland), 2023, 13, 221-228.	3.1	17
2	Interfacial and structural analysis of MeV heavy ion irradiated SiC. Applied Nanoscience (Switzerland), 2023, 13, 3181-3188.	3.1	15
3	Defect levels in high energy heavy ion implanted 4H-SiC. Materials Letters, 2022, 308, 131150.	2.6	18
4	LnFe _{0.5} Cr _{0.5} O ₃ based perovskites showing multiferroic properties and polarization induced photoelectrochemical activity. Journal of Solid State Chemistry, 2021, 299, 122200.	2.9	3
5	Excellent UV-Light Triggered Photocatalytic Performance of ZnO:SiO ₂ Nanocomposite for Water Pollutant Compound Methyl Orange Dye. Nanomaterials, 2021, 11, 2548.	4.1	38
6	Investigation of structural and impedance spectroscopic properties of borate glasses with high Li ⁺ concentration. Solid State Ionics, 2021, 368, 115704.	2.7	17
7	Epitaxial 4H-SiC based Schottky diode temperature sensors in ultra-low current range. Vacuum, 2020, 182, 109590.	3.5	46
8	Electronic transport in epitaxial 4H-SiC based Schottky diodes modified selectively by swift heavy ions. Materials Science in Semiconductor Processing, 2020, 115, 105108.	4.0	26
9	Tailoring Surface and Electrical Properties of Ni/4H-nSiC Schottky Barrier Diodes via Selective Swift Heavy Ion Irradiation. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700555.	1.8	24
10	Improvement in reverse bias leakage current of Ni/4H-nSiC Schottky barrier diodes via MeV selective ion irradiation. IOP Conference Series: Materials Science and Engineering, 2018, 331, 012016.	0.6	12
11	Capacitance roll-off and frequency dispersion capacitance-conductance phenomena in field plate and guard ring edge-terminated Ni/SiO ₂ /4H-nSiC Schottky barrier diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 193-202.	1.8	39
12	Diameter dependent thermal sensitivity variation trend in Ni/4H-SiC Schottky diode temperature sensors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2015, 33, .	1.2	34
13	Barrier height inhomogeneities induced anomaly in thermal sensitivity of Ni/4H-SiC Schottky diode temperature sensor. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, .	1.2	55
14	Selective SHI irradiation for mesa type edge termination in semiconductor planar junction. Journal of Physics: Conference Series, 2013, 423, 012057.	0.4	15